

Low Noise Amplifier, 40-53GHz

Performance characteristics

- ✧ Frequency range: 40GHz~53GHz
- ✧ Small signal gain: 21dB
- ✧ Noise figure: 1.9dB
- ✧ P1dB: 4dBm
- ✧ DC Supply: Vd=5V@Id=13mA
- ✧ Dimensions: 1.10 mm×0.75 mm×0.07 mm

Product Description

GLA-4753 is an Q-band broadband low noise amplifier chip with a frequency range of 40GHz~53GHz, small signal gain of 21dB and a typical noise figure of 1.9dB. This chip operates from a single +5 V power supply.

Electrical Specifications

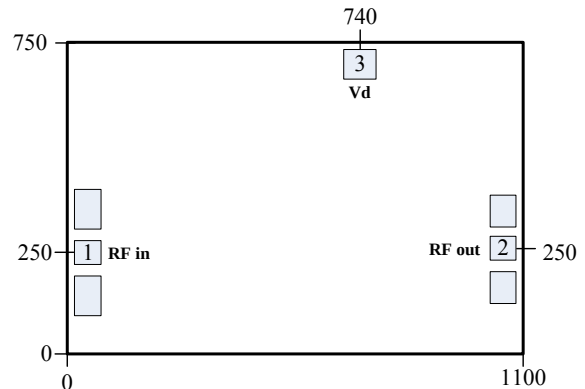
(Vd=5V, I d=11mA, T A=+25°C)

Parameter	Min	Typ	Max	Unit
Frequency range	40		53	GHz
Small signal gain		21		dB
Gain flatness		±0.5		dB
Noise figure		1.9		dB
P1dB		4		dBm
Input VSWR		1.8		-
Output VSWR		1.8		-
Quiescent Current		13		mA

Absolute Maximum Ratings

Maximum Drain Voltage	8V
Maximum Input RF Power	15dBm
Storage Temperature	-65°C~150°C
Operating Temperature	-55°C~85°C

Die Outline Dimensions

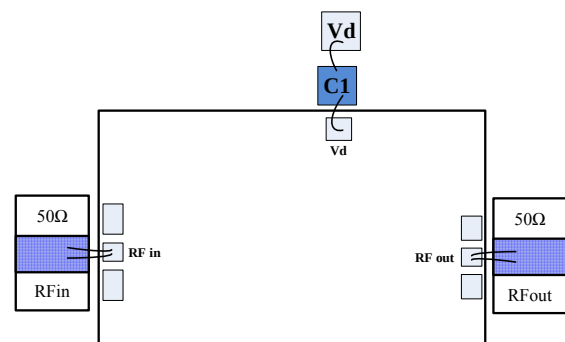


- Notes: 1) All dimensional units are micrometers (μm).
 2) Tolerance for die length and width: ±50 μm.
 3) Die thickness: 70 μm

Bond Pad Definition

No.	Symbol	Function Description	Pad Size(μm ²)
1	RFin	RF input port, matched to 50Ω system. No series DC blocking capacitor required	80×80
2	RFout	RF output port, matched to 50Ω system. No series DC blocking capacitor required	80×80
3	Vd	Drain bias supply pin; 100 pF, a 100 pF bypass capacitor shall be externally fitted.	100×100

Recommended Assembly Schematic

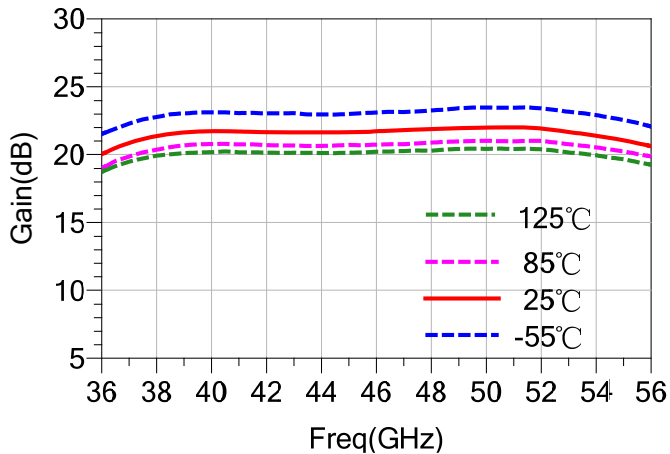


Note: The peripheral capacitor C1 has a capacitance of 100 pF. A single-layer capacitor is recommended for C1 and should be placed as close as possible to the chip bonding pads.

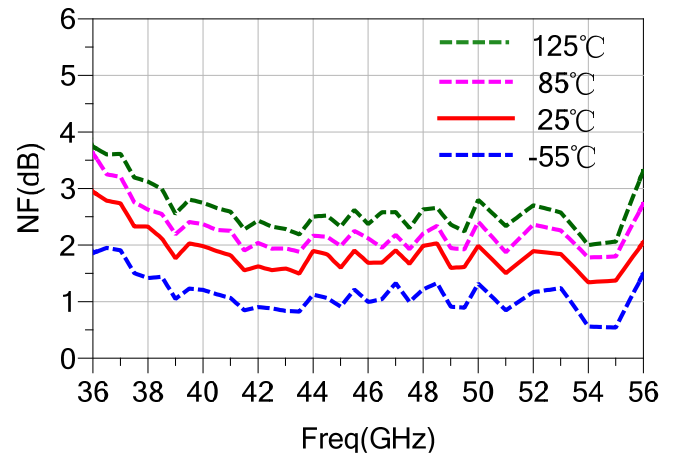
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On-Wafer Measurement Curves $V_d=5V$, $I_d=13mA$

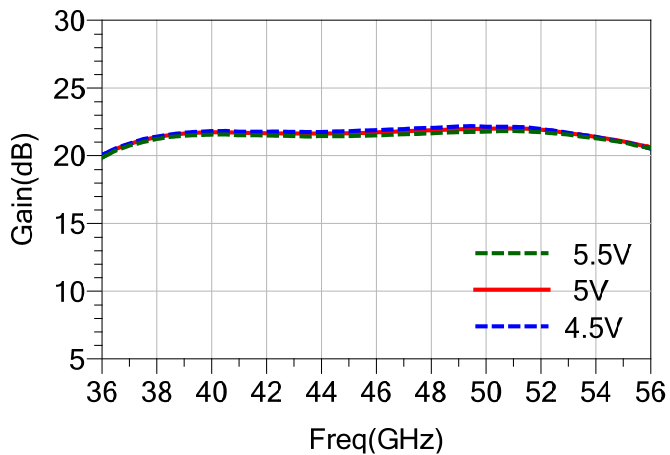
Small Signal Gain vs. Frequency



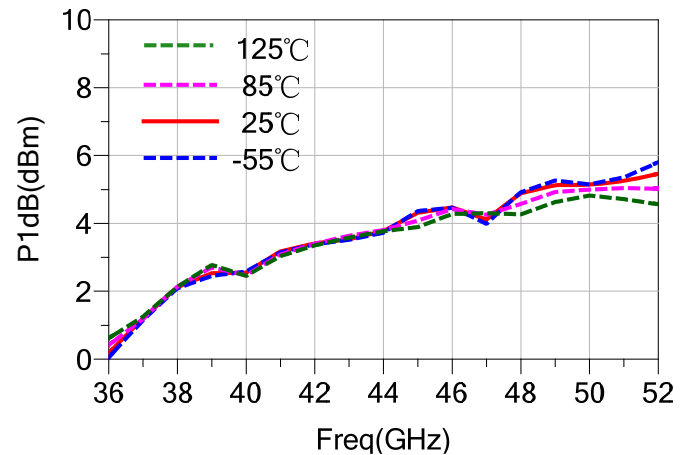
Noise Figure vs. Frequency



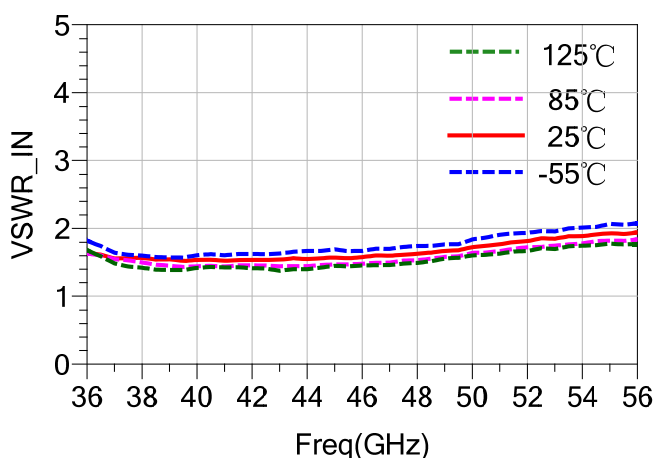
Small-signal gain vs. voltage



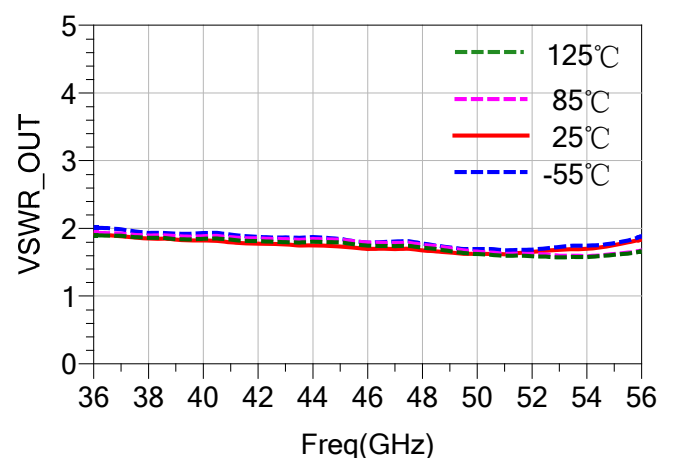
P1dB vs. Frequency



Input VSWR vs. Frequency



Output VSWR vs. Frequency



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Handling & Operating Precautions

- 1) Storage: Dies must be stored in ESD-protected containers under nitrogen atmosphere.
- 2) Cleaning: All die handling shall be performed in a cleanroom environment. Liquid cleaning solvents are prohibited for die cleaning. die handling shall be performed in a cleanroom environment. Liquid cleaning solvents are prohibited for die cleaning.
- 3) ESD Protection: Strictly follow all ESD control protocols to prevent electrostatic damage to the die.
- 4) General Handling: Handle dies only with vacuum pick-up tools or precision fine-tip tweezers. Avoid contact between tools/fingers and the die surface.
- 5) Power-up & Power-down Sequence: Power-up: Apply gate voltage first, then drain voltage. Power-down: Remove drain voltage first, then gate voltage.
- 6) Die Mounting: Two acceptable processes are AuSn eutectic sintering or conductive epoxy bonding. The mounting substrate surface must be clean and flat; minimize the gap between the die and RF input/output substrate traces.
 - Sintering Process: Use 80/20 AuSn solder. Sinter temperature shall not exceed 300 °C, total sinter time ≤20 seconds, scrub time ≤3 seconds.
 - Epoxy Bonding: Apply minimal conductive epoxy dosage; follow curing specifications provided by epoxy supplier.
- 7) Wire Bonding Requirements:
 - Unless otherwise specified, use two 25µm diameter gold bonding wires for RF input and output, with shortest possible wire length.
 - Thermosonic bonding temperature: 150 °C; use minimum feasible ultrasonic power.
- 8) Contact your supplier for technical support if any issues occur.